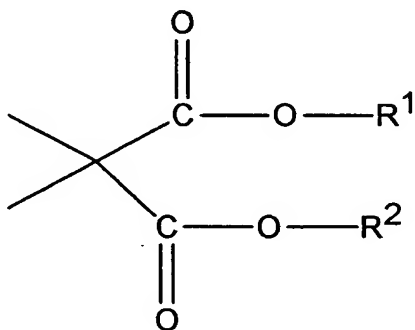


CLAIMS

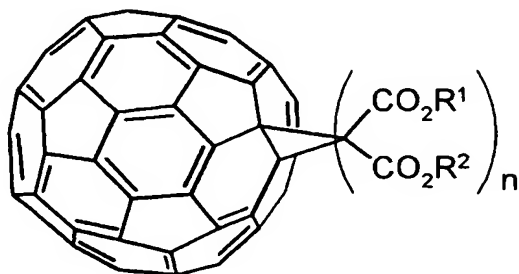
1. A photoresist composition, comprising: a fullerene derivative (A) having two or more malonic ester residues.
2. The photoresist composition according to Claim 1, wherein the malonic ester residue is the group expressed by the general formula (1) below,



(1)

in which, R^1 and R^2 independently represent an alkyl group, which may be identical or different from each other.

3. The photoresist composition according to Claim 1, in which the fullerene derivative (A) is a compound, expressed by the general formula (2) below,



(2)

in which, n is an integer of 2 or more, and R^1 and R^2 independently represent an alkyl group, which may be identical or different from each other.

4. The photoresist composition according to Claim 3, wherein the alkyl group has a normal or branched chain, or cyclic alkyl group having 1 to 10 carbons, and n is an integer from 2 to 10.

5. The photoresist composition according to Claim 1, comprising the fullerene derivative (A), a radiation sensitive acid generator (B), and an organic solvent.

6. The photoresist composition according to Claim 5, further comprising a film forming resin component (C).

7. The photoresist composition according to Claim 6, wherein the photoresist composition is positive-type, and the film formation resin component (C) has an acid-dissociative dissolution-controlling group, which is a resin (C1) that increases solubility to alkali by acid action.

8. The photoresist composition according to Claim 6, wherein the photoresist composition is negative-type, the component (C) is an alkaline soluble resin (C2) and a crosslinking agent component (D).

9. The photoresist composition according to Claim 1, further comprising a nitrogen-containing organic compound.

10. The photoresist composition according to Claim 1, further comprising an organic carboxylic acid.

11. A method for forming the resist pattern, comprising steps of:

coating the photoresist composition according to Claim 1 onto a substrate to form a resist film,
exposing the resist pattern, and
developing the photoresist film after the exposure to form a resist pattern.